

**Silicon PNP Power Transistors**

**2SA1279**

**DESCRIPTION**

- With TO-220F package
- Low collector saturation voltage

**APPLICATIONS**

- High current switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

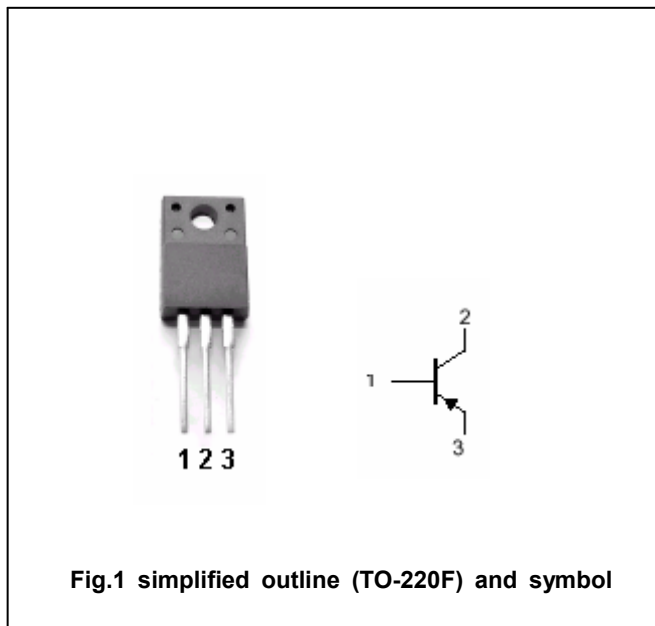


Fig.1 simplified outline (TO-220F) and symbol

**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-60	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-5	A
I <sub>CM</sub>	Collector current-peak		-8	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	30	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-60			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A;I <sub>B</sub> =-0.15A			-0.4	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-3A;I <sub>B</sub> =-0.15A			-1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-60V;I <sub>E</sub> =0			-1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-1	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-1V	70		240	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-1V	30			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-4V		60		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V;f=1MHz		200		pF

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PACKAGE OUTLINE

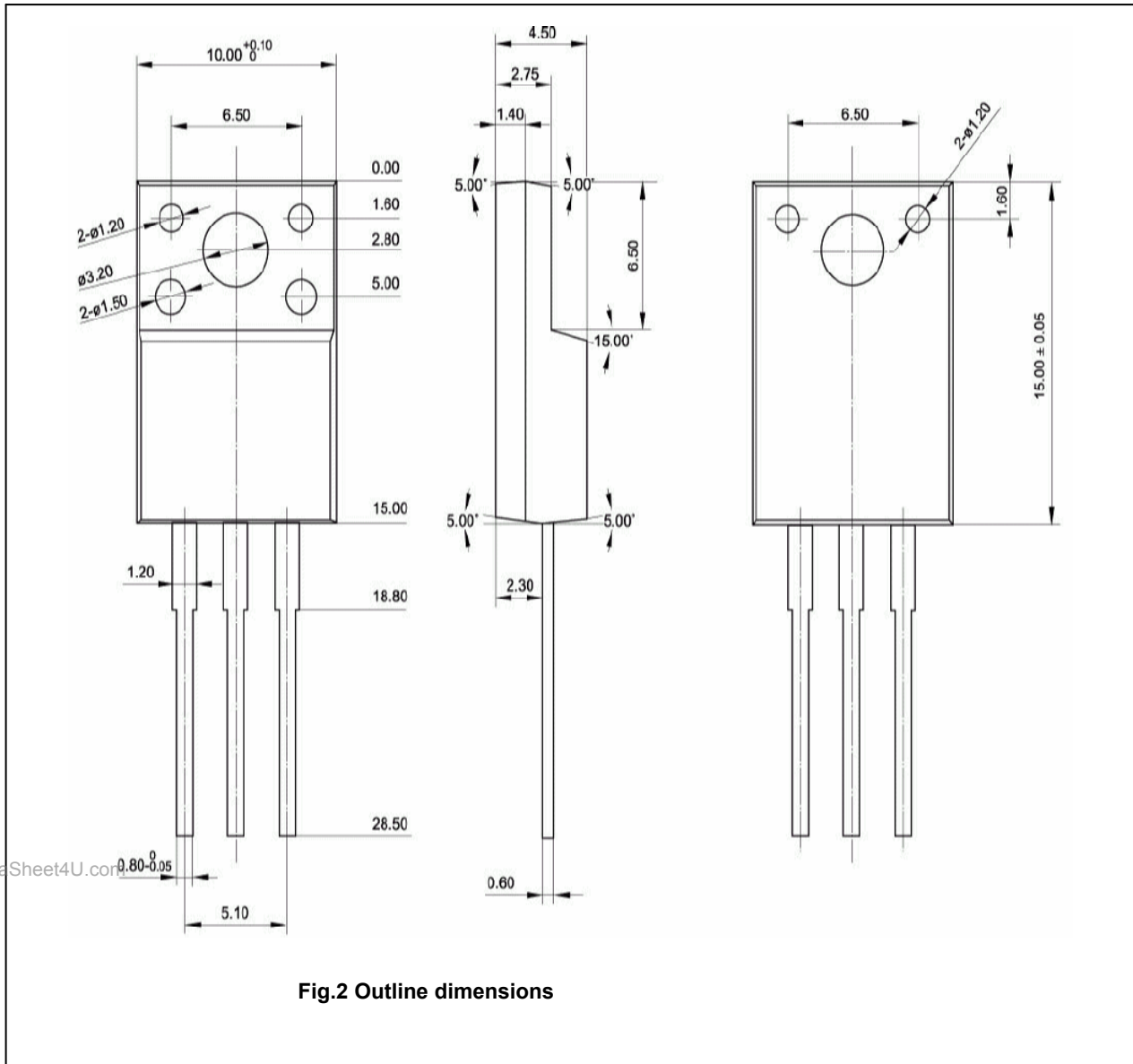


Fig.2 Outline dimensions